

IN THE CLAIMS

1. (Canceled) A method for reconstructing an integrated circuit package comprising:
 - deconstructing an integrated circuit package for exposing a wire bond pad and a lead frame located therein;
 - attaching a die to the exposed wire bond pad of the lead frame so that the second die is electrically connected to the lead frame;
 - encapsulating the die and the wire bond pads in an encapsulant; and
 - reshaping an upper surface of the encapsulant where at least a portion of the encapsulant reshaping is performed by a lapping process.
2. (Currently Amended) A method according to claim 1, wherein lapping is performed by an abrasive or ablative lapping process.
3. (Currently Amended) A method according to claim 1, wherein lapping is performed by a mechanical, chemical, or electromagnetic lapping process.
4. (Currently Amended) A method according to claim 1, wherein encapsulating the die and the wire bond pads results in the encapsulant having a convex or concave an upper surface, and reshaping the encapsulant results in the encapsulant having a planar an upper surface.
5. (Currently Amended) A method according to claim 1, further comprising marking the reshaped upper surface of the encapsulant.
6. (Currently Amended) A method according to claim 1, wherein the reshaped upper surface of the encapsulant is sufficiently flat to permit labeling by printing, photolithographic or mechanical marking techniques to simulate a production transfer molded encapsulated IC package, the method further comprising marking the reshaped upper surface of the encapsulant.

7. (Currently Amended) A method according to claim 1 ~~10~~, wherein the lapping process is performed in conjunction with using a laser or another source of electromagnetic radiation.

8. (Currently Amended) A method according to claim 1 ~~10~~, wherein the lapping process comprises using a planar abrasive surface.

9. (Currently Amended) A method according to claim 1 ~~10~~, wherein the lapping process comprises using a planar abrasive surface attached to a wheel or belt.

10. (Currently Amended) ~~A method according to claim 1~~ A method for reconstructing an integrated circuit package comprising:
deconstructing an integrated circuit package for exposing a wire bond pad and a lead frame located therein;
attaching a die to the wire bond pad so that the die is electrically connected to the lead frame;
encapsulating the die and the wire bond pad in an encapsulant to form a first encapsulated package;
providing a second encapsulated package that is encapsulated separately from the first encapsulated package; and
reshaping the first encapsulated package and the second encapsulated package at the same time by using a lapping process, wherein the lapping process is performed using a planar abrasive surface sufficiently large to permit the first encapsulant and the second encapsulant ~~more than one package~~ to be lapped at the same time.

11. (Currently Amended) A method according to claim 1 ~~10~~, wherein the lapping process is performed in conjunction with chemical etching.

12. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed in conjunction with using a gas-jet or liquid-jet containing a particular material.
13. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed via a mechanical grind.
14. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed using a combination of mechanical and chemical ablation.
15. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed using a combination of mechanical and electromagnetic ablation.
16. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed in conjunction with using laser ablation.
17. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed using a combination of electromagnetic and chemical ablation.
18. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed in conjunction with impinging an ultra-fine particulate using a high pressure gas-jet against the material to be lapped.
19. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed in conjunction with impinging an ultra-fine particulate under high pressure against the material to be lapped.
20. (Currently Amended) A method according to claim \pm 10, wherein the lapping process is performed in conjunction with delivering a pulsating liquid-jet under high pressure against the material to be lapped.

21. (Currently Amended) A method according to claim 4 10, wherein the lapping process is performed in conjunction with plasma etching.

22. (Currently Amended) A method according to claim 4 10, wherein the lapping process is performed in conjunction with using a pressurized liquid against the material to be lapped.